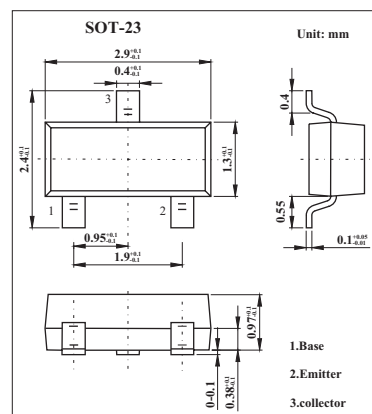


PNP Silicon Epitaxial Transistor

2SA1365

■ Features

- Low collector to emitter saturation voltage.
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting.
- High collector current.
- High gain band width product.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-4	V
Peak collector current	I_{CM}	-1	A
Collector current	I_C	-700	mA
Collector dissipation ($T_a=25^\circ\text{C}$)	P_C	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\ \mu\text{A}, I_E = 0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -100\ \mu\text{A}, R_{BE} = \infty$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\ \mu\text{A}, I_C = 0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB} = -25\ \text{V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -2\ \text{V}, I_C = 0$			-1	μA
DC current gain (*)	h_{FE}	$V_{CE} = -4\ \text{V}, I_C = -100\ \text{mA}$	150		800	
Collector-emitter saturation voltage	V_{CE}	$I_C = -500\ \text{mA}, I_B = -25\ \text{mA}$		-0.2	-0.5	V
Gain band width product	f_T	$V_{CE} = -6\ \text{V}, I_E = 10\ \text{mA}$		180		MHz

* It shows h_{FE} classification in right table.

■ h_{FE} Classification

Marking	AE	AF	AG
h_{FE}	150~300	250~500	400~800